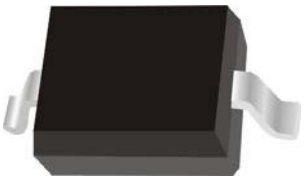
PESD5V0L1BA-N

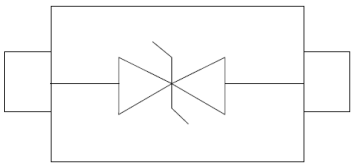
TVS Diode

Features

- 150 Watts peak pulse power (tp = 8/20μs)
- Transient protection for high speed data lines to IEC 61000-4-2 (ESD) ±15kV (air), ±8kV (contact) IEC 61000-4-4 (EFT) 40A (5/50ns)
- Protects One Power or I/O Port
- Low leakage current
- Low operating and clamping voltages
- Solid-state silicon avalanche technology



SOD323



Applications

- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Portable Instrumentation
- Personal Digital Assistant (PDA)

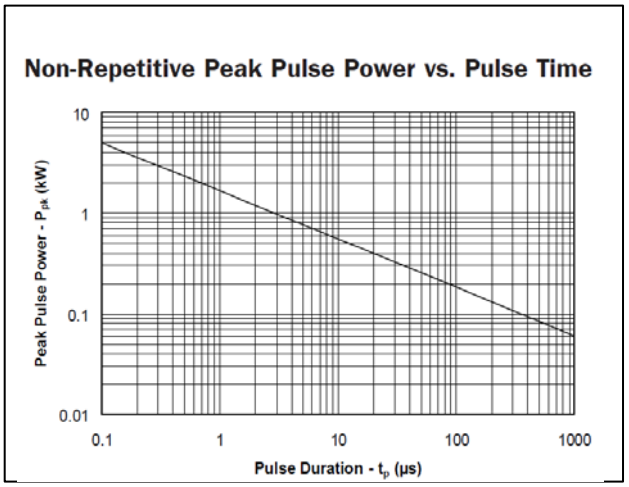
Maximum Rating @ Ta=25℃ unless otherwise specified

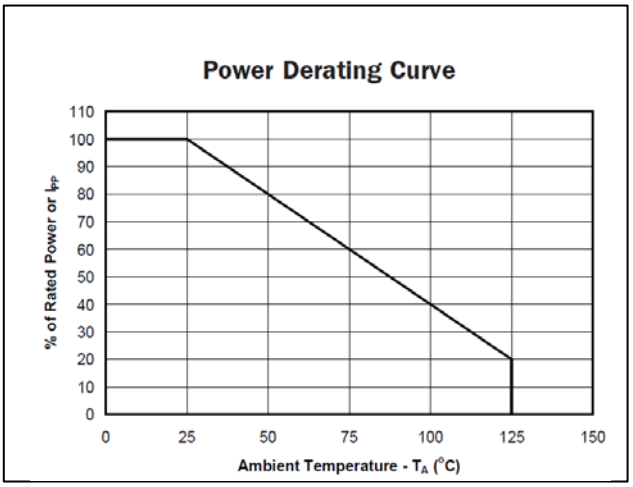
Symbol	Parameter	Ratings	Units
P_{PK}	Peak Pulse Power (tp = 8/20μs)	150	Watts
T_L	Lead Soldering Temperature	260(10sec.)	℃
T_J	Operating Temperature	-55 to +125	℃
T_{STG}	Storage Temperature	-55 to +150	℃

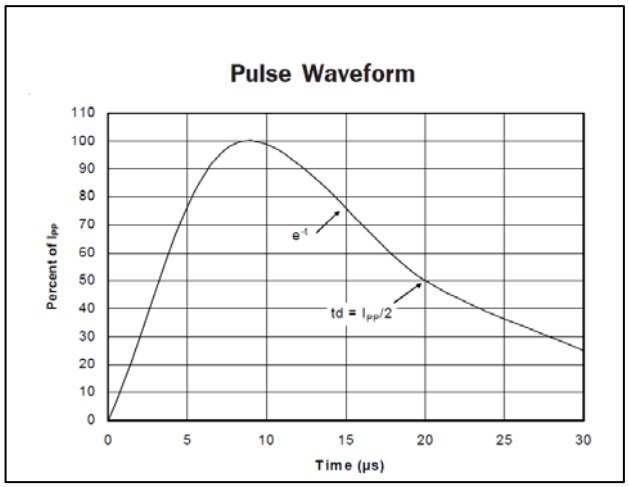
Electrical Characteristics@ Ta=25℃ unless otherwise

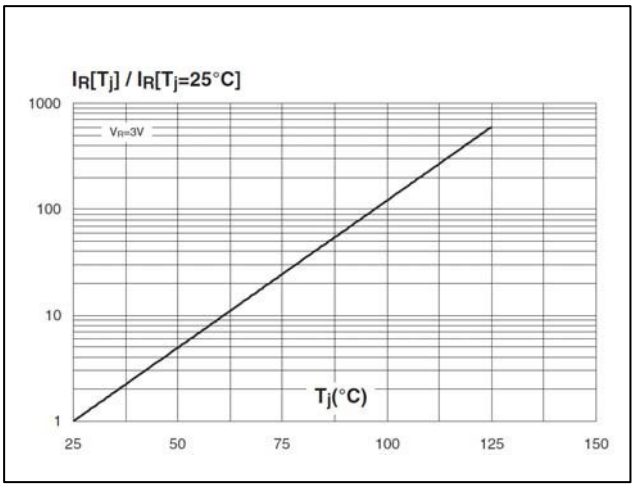
Parameter	VRWM @IR		VBR@ImA	VC@1A	VC@IPP		CJ
	V	μA	V	V	V	A	pF
		MAX	MIN	MAX	MAX		TYP
PESD5V0L1BA-N	5	1	5.8	11.8	15	3	3

Typical Characteristics@ Ta=25℃ unless otherwise specified



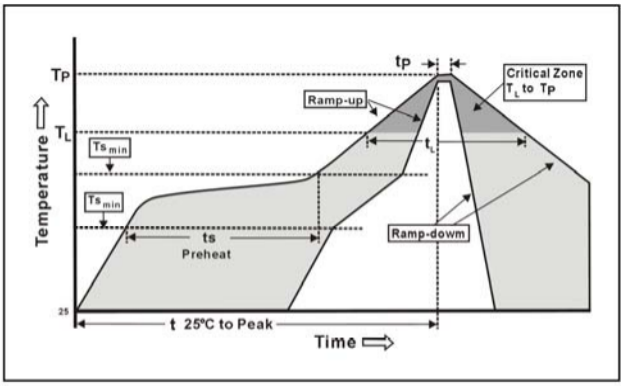






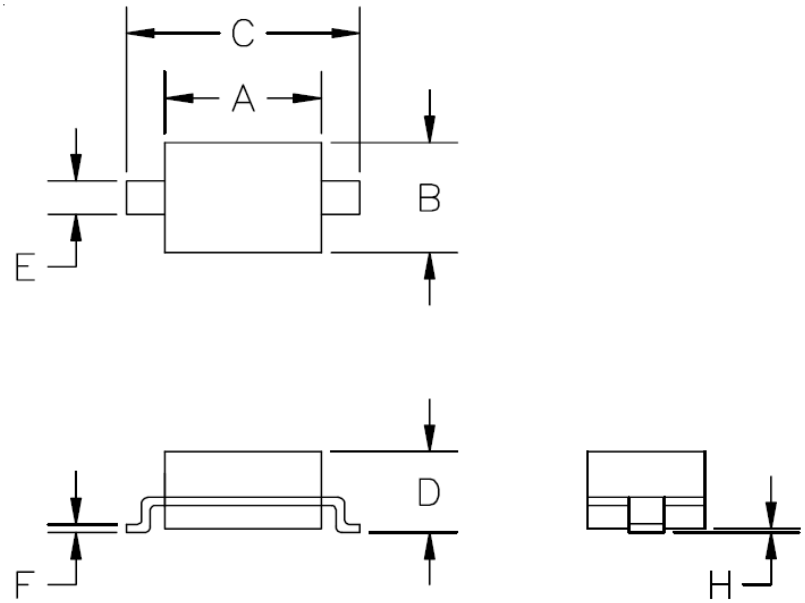
Soldering Parameters

Reflow Condition		Fb – Free assembly
Pre Heat	-Temperature Min ($T_{s(Min)}$)	150°C
	-Temperature Max ($T_{s(Max)}$)	200°C
	-Time (Min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus) Temp (T_L) to peak		3°C/second Max
$T_{S(Max)}$ to T_L - Ramp-up Rate		3°C/second Max
Reflow	-Temperature (T_L) (Liquidus)	217°C
	-Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		$250^{+0/-5}$ °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-dowm Rate		6°C/second Max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		260°C



Package Outline

Plastic surface mounted package **SOD323**



DIMENSIONS				
DIM N	INCHES		MM	
	MIN	MAX	MIN	MAX
A	.060	.071	1.5	1.8
B	.045	.054	1.2	1.4
C	.090	.107	2.3	2.7
D	–	.043	–	1.1
E	.012	.016	0.3	0.4
F	.004	.010	.10	.25
H	–	.004	–	.10